



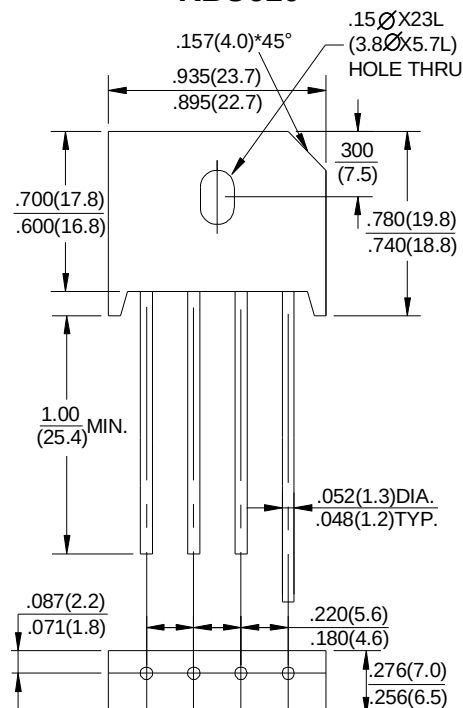
SILICON BRIDGE RECTIFIERS

REVERSE VOLTAGE - 50 to 1000Volts
FORWARD CURRENT - 6.0 Amperes

FEATURES

- Surge overload rating -175 amperes peak
- Ideal for printed circuit board
- Reliable low cost construction utilizing molded plastic technique
- Plastic material has UL
- Mounting postition:Any
- Mounting torque:5 In.lb.Max

KBU610



Dimensions in inches and (milimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave ,60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

CHARACTERISTICS	SYMBOL	KBU6005	KBU601	KBU602	KBU604	KBU606	KBU608	KBU610	UNIT
Maximum Recurrent Peak Reverse Voltage	VRRM	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	VRMS	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	VDC	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Output Current at Tc=100°C	I(AV)	6.0							A
Peak Forward Surge Current 8.3ms single Half Sine-Wave Super Imposed on Rated Load (JEDEC Method)	IFSM	175							A
Maximum Instantaneous Forward Voltage Drop per Element at 3.0A	VF	1.0							V
Maximum Reverse Leakage at rated Tj=25°C DC Blocking Voltage Per Element Tj=100°C	IR	10 200							µA
Typical Junction Capacitance Per Element (Note1)	CJ	260							pF
Operating Temperature Range	TJ	-55 to +150							°C
Storage Temperature Range	TSTG	-55 to+150							°C

Note:1.Measured at 1.0MHz and applied reverse voltage of 4.0V DC.



FIG.1-DERATING CURVE FOR
OUTPUT RECTIFIED CURRENT

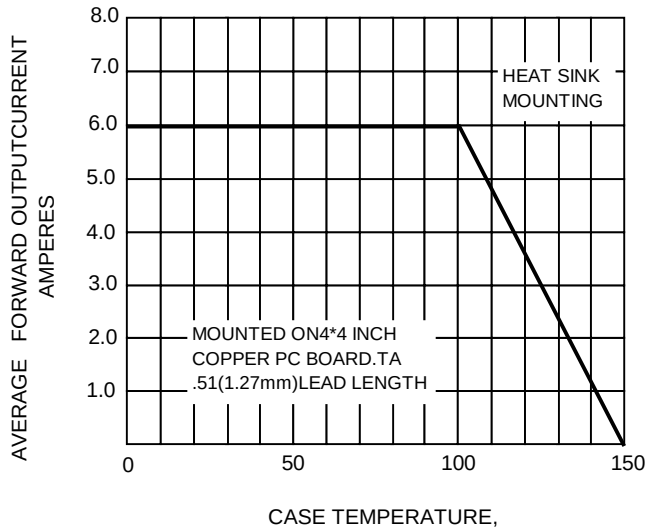


FIG.2 TYPICAL INSTANTANEOUS FORWARD
CHARACTERISTIC

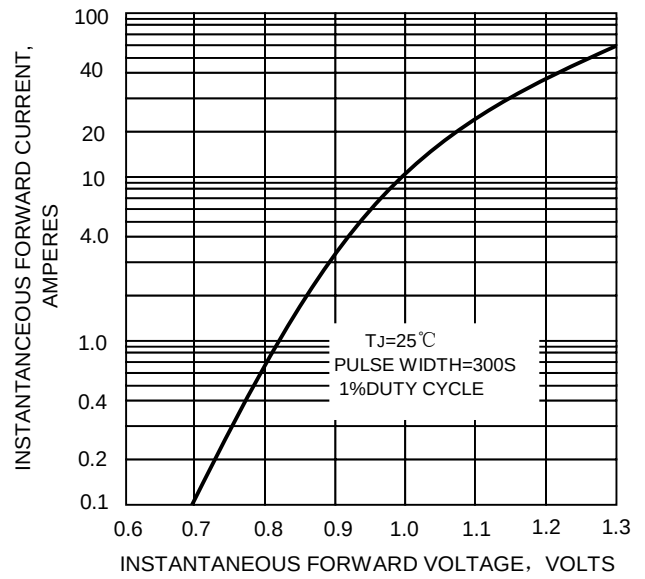


FIG.3-MAXIMUM NON-RETETITIVE PEAK
FORWARD SURGE CURRENT

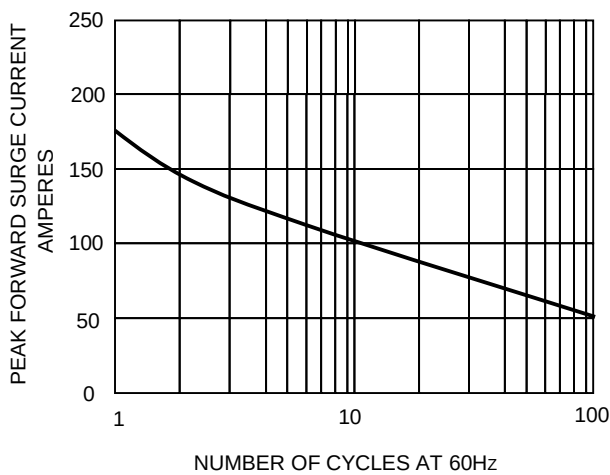


FIG.4-TYPICAL REVERSE
CHARACTERISTICS

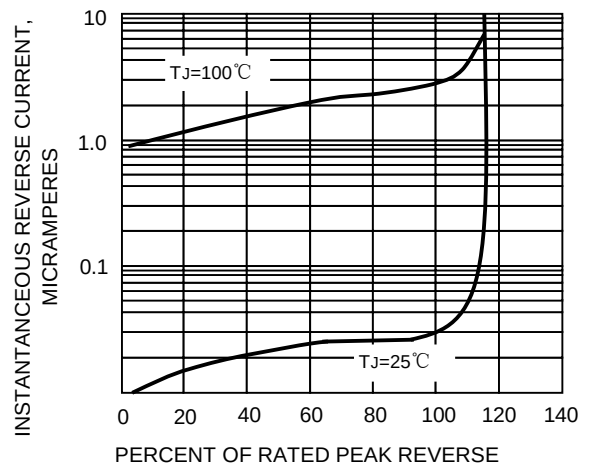


FIG.5-TYPICAL JUNCTION CAPACITANCE PER ELEMENT

